

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S20	24620	semiconductor and (MOSFET or MOS or FET or IGBT or transistor) and ((length or thickness) with substrate) and (vertical or vertically)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/26 18:49
S21	35908	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and ((length or thickness) with substrate) and @ad<"20031205"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/26 18:51
S22	20892	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and ((length or thickness) near5 substrate) and @ad<"20031205"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/26 18:51
S23	1402	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and (((length or thickness) near5 substrate) with (total or entire or all)) and @ad<"20031205"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/30 07:15
S24	0	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and (((hieght) near5 substrate) with (total or entire or all)) and @ad<"20031205"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/26 19:30
S25	76	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and (((height) near5 substrate) with (total or entire or all)) and @ad<"20031205"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/26 19:30
S26	1799	(257/327-329).ccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/26 19:32
S27	913	(257/341).ccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/26 19:34
S28	1245	(257/368).ccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/26 19:35

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S29	121	(257/502).cccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/26 19:41
S30	646	(257/508 or 257/520).cccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/26 19:41
S31	387	(257/621).cccls. and @ad<"20031205"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/30 00:34
S32	24972408	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and ((region or zone or layer) with cylinder or cylindrical) @ad<"20031205"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/30 07:16
S33	2413	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and ((region or zone or layer) with (cylinder or cylindrical)) and @ad<"20031205"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/30 07:20
S34	282	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and ((diffusion or doped) with (cylinder or cylindrical)) and @ad<"20031205"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/30 07:33
S35	459	semiconductor and (MOSFET or MOS or FET or IGBT or bipolar) and ((diffusion or doped) with (annular)) and @ad<"20031205"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/05/30 07:34